General Description

The AGMH056N08A combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

This device is ideal for load switch and battery protection applications.

Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance
- 100% Avalanche tested
- 100% DVDS tested

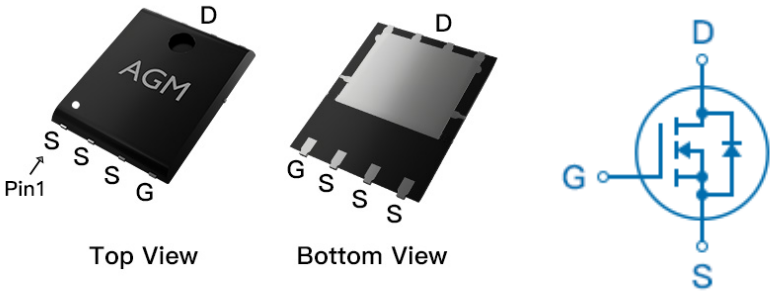
Application

- MB/VGA Vcore
- SMPS 2nd Synchronous Rectifier
- POL application
- BLDC Motor driver

Product Summary

BVDSS	RDSON	ID
85V	4.8mΩ	142A

PDFN5*6 Pin Configuration



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AGMH056N08A	AGMH056N08A	PDFN5*6	330mm	12mm	3000

Table 1. Absolute Maximum Ratings (TA=25℃)

Symbol	Parameter	Value	Unit
VDS	Drain-Source Voltage (VGS=0V)	85	V
VGS	Gate-Source Voltage (VDS=0V)	±20	V
ID	Drain Current-Continuous(Tc=25℃) **(Note 1)**	142	A
	Drain Current-Continuous(Tc=100℃)	85	A
IDM (pluse)	Drain Current-Pulsed **(Note 2)**	568	A
PD	Maximum Power Dissipation(Tc=25℃)	288	w
	Maximum Power Dissipation(Tc=100℃)	144	w
EAS	Avalanche energy **(Note 3)**	400	mJ
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 175	℃

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
RθJA	Thermal Resistance Junction-ambient (Steady State)[1]	---	20	℃/W
RθJC	Thermal Resistance Junction-Case[1]	---	0.52	℃/W

Table 3. Electrical Characteristics (TJ=25℃unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BV_{DSS}	Drain-Source Breakdown Voltage	VGS=0V ID=250μA	85	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=85V,VGS=0V	--	--	1	μA
IGSS	Gate-Body Leakage Current	VGS=±20V,VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS,ID=250μA	2.1	2.6	3.3	V
gFS	Forward Transconductance	VDS=5V,ID=20A	--	24	--	S
RDS(on)	Drain-Source On-State Resistance	VGS=10V, ID=20A	--	4.8	6.1	mΩ
Dynamic Characteristics						
Ciss	Input Capacitance	VDS=40V,VGS=0V, F=1MHZ	--	1973	--	pF
Coss	Output Capacitance		--	795	--	pF
Crss	Reverse Transfer Capacitance		--	25	--	pF
Rg	Gate resistance	VGS=0V, VDS=0V,f=1.0MHz	--	0.8	--	Ω
Switching Times						
td(on)	Turn-on Delay Time	VGS=10V,VDS=40V, ID=40A,RGEN=3Ω	--	15	--	nS
tr	Turn-on Rise Time		--	52	--	nS
td(off)	Turn-Off Delay Time		--	38	--	nS
tf	Turn-Off Fall Time		--	24	--	nS
Qg	Total Gate Charge	VGS=40V, VDS=10V, ID=40A	--	57	--	nC
Qgs	Gate-Source Charge		--	19	--	nC
Qgd	Gate-Drain Charge		--	14	--	nC
Source-Drain Diode Characteristics						
ISD	Source-Drain Current(Body Diode)		--	--	142	A
VSD	Forward on Voltage	VGS=0V,IS=20A	--	--	1.2	V
trr	Reverse Recovery Time	Is=20A , dI/dt=100A/μs ,TJ=25℃	--	52	--	ns
Qrr	Reverse Recovery Charge		--	65	--	nc

Notes 1.The maximum current rating is package limited.

Notes 2.Repetitive Rating: Pulse width limited by maximum junction temperature

Notes 3.EAS condition: TJ=25℃,VDD=40V,Vgs=10V,ID=40A, L=0.5mH,RG=25ohm

Typical Characteristics

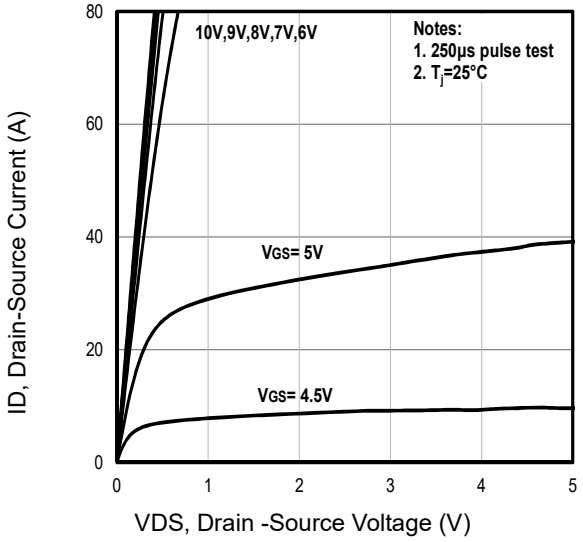


Fig1. Typical Output Characteristics

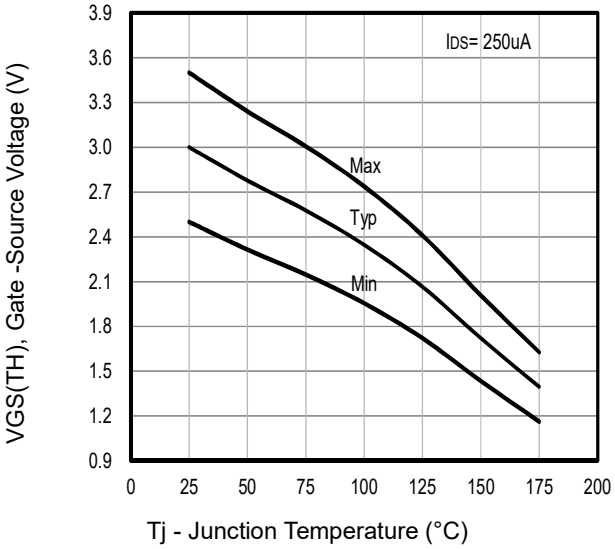


Fig2. Typical $V_{GS(TH)}$ Gate -Source Voltage Vs. Tj

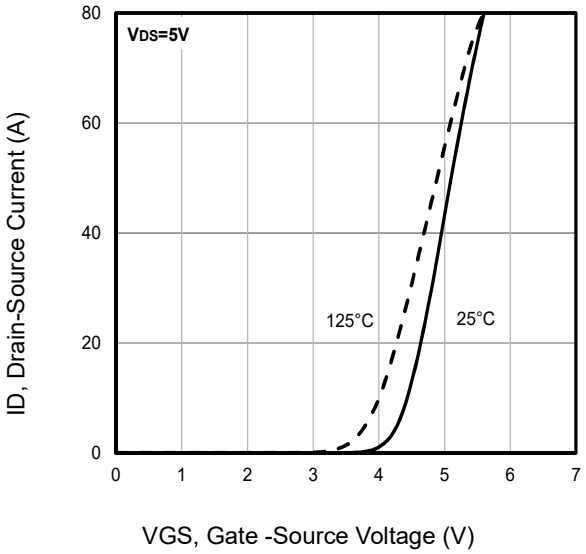


Fig3. Typical Transfer Characteristics

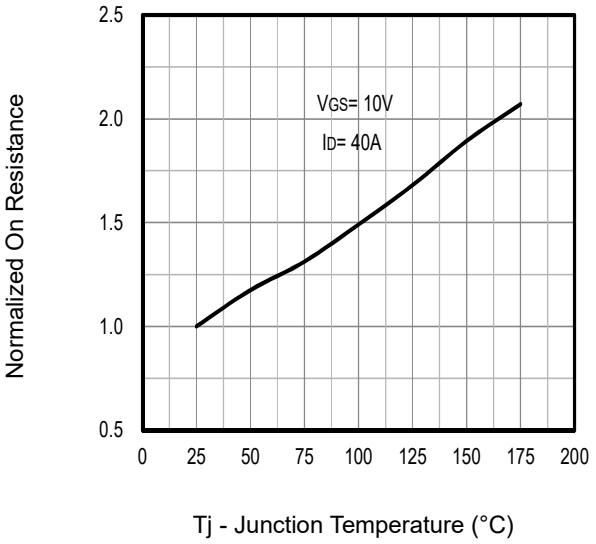


Fig4. Typical Normalized On-Resistance Vs. Tj

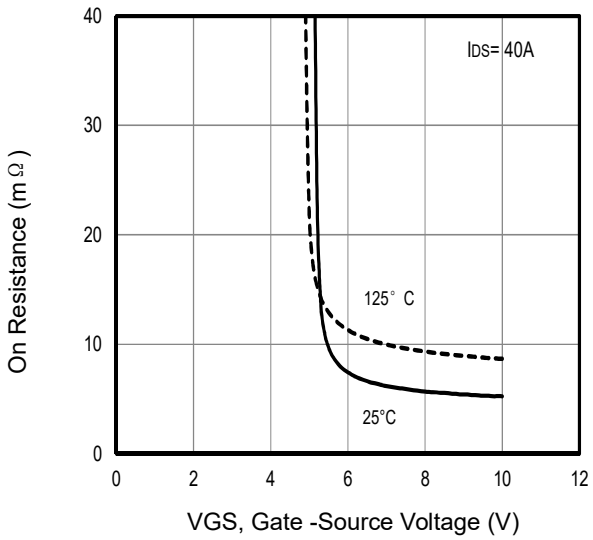


Fig5. Typical On Resistance Vs Gate -Source Voltage

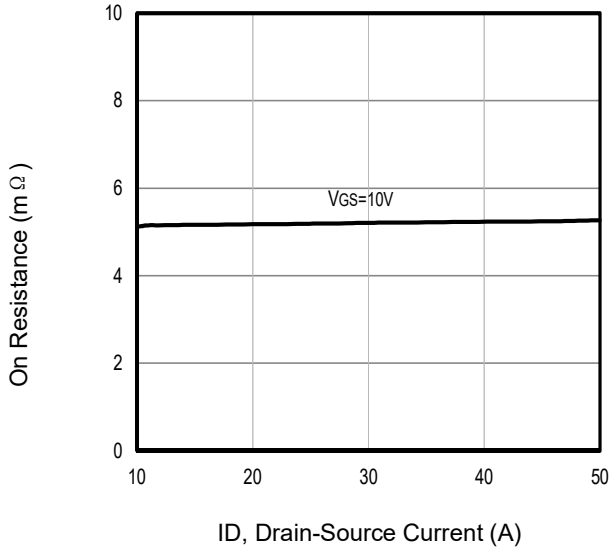


Fig6. Typical On Resistance Vs Drain Current

Typical Characteristics

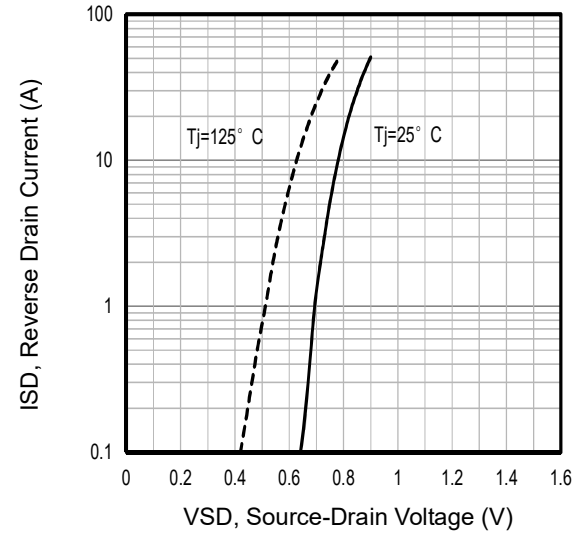


Fig7. Typical Source-Drain Diode Forward Voltage

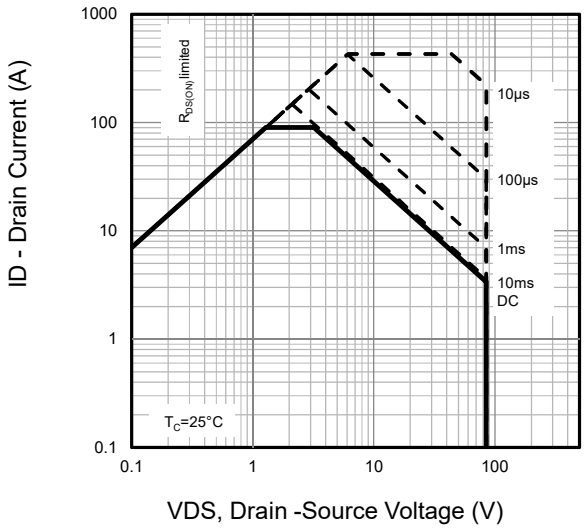


Fig8. Maximum Safe Operating Area

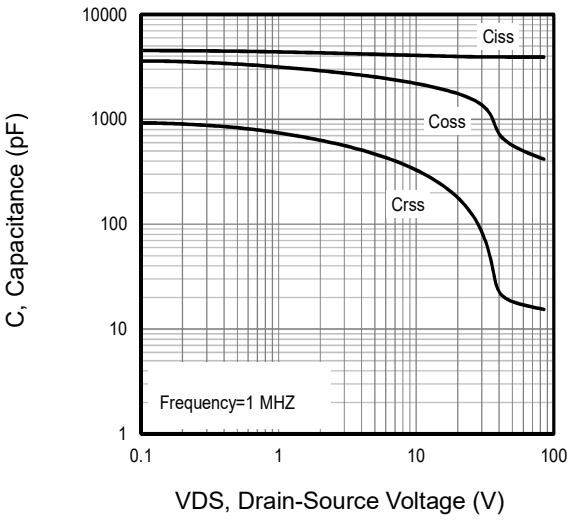


Fig9. Typical Capacitance Vs. Drain-Source Voltage

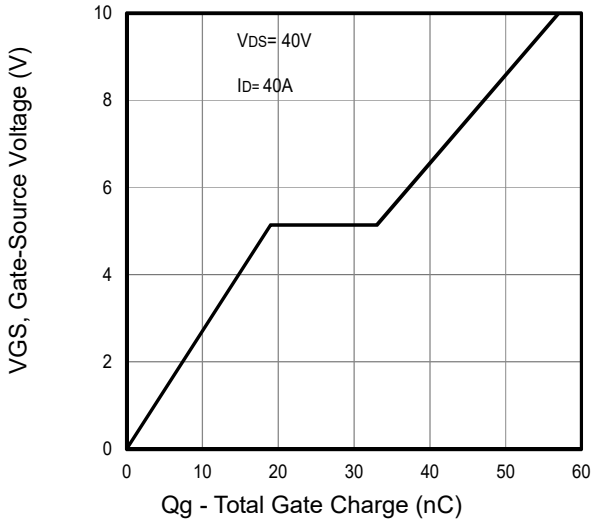


Fig10. Typical Gate Charge Vs. Gate-Source Voltage

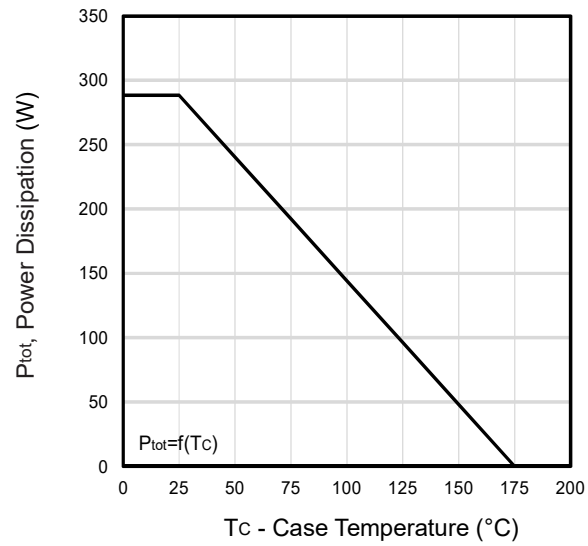


Fig11. Power Dissipation Vs. Case Temperature

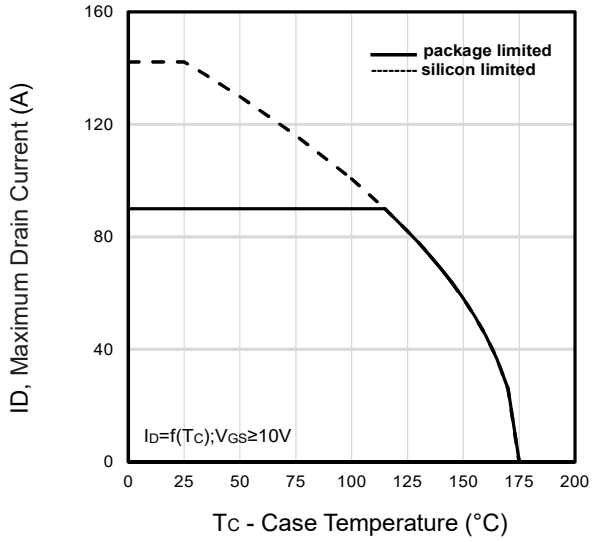


Fig12. Maximum Drain Current Vs. Case Temperature

Typical Characteristics

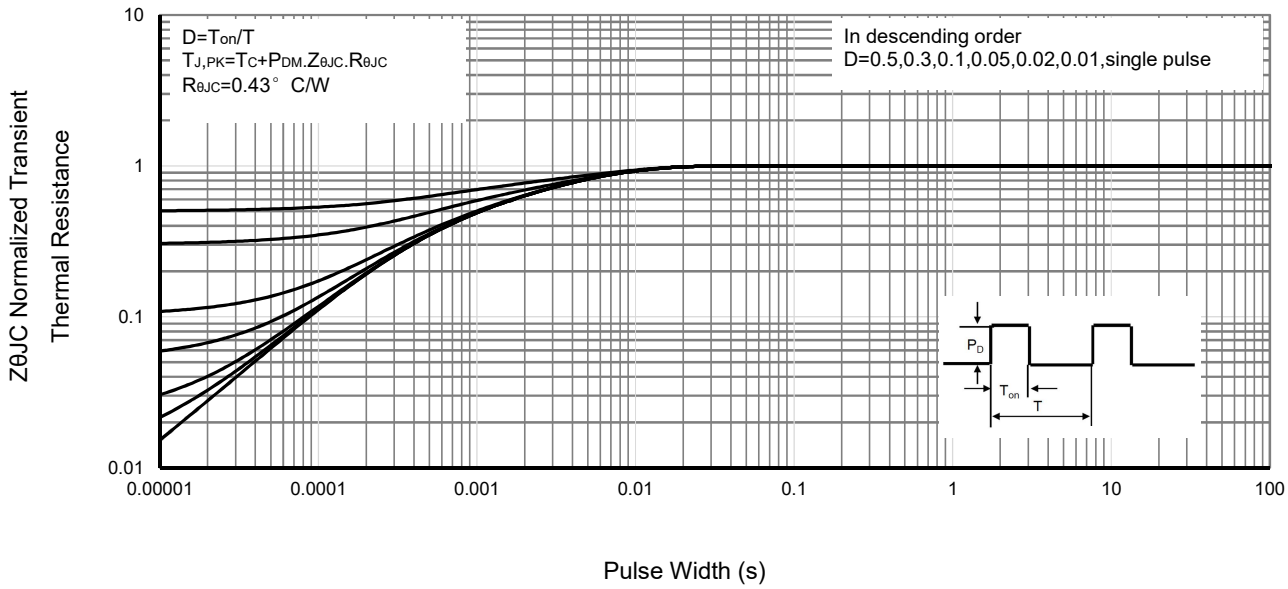


Fig13 . Normalized Maximum Transient Thermal Impedance

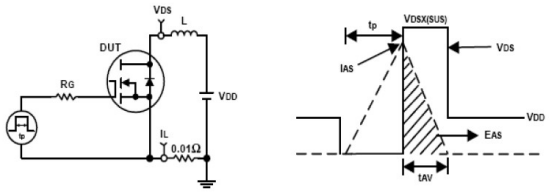


Fig14. Unclamped Inductive Test Circuit and waveforms

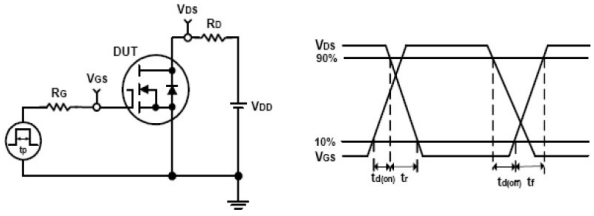
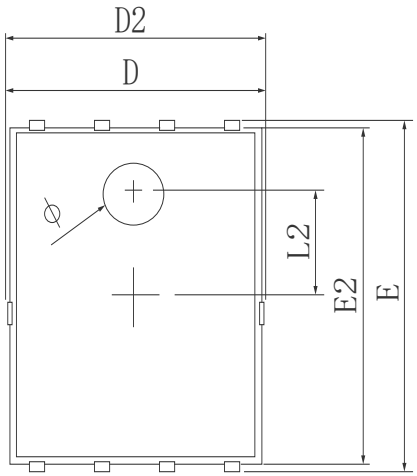
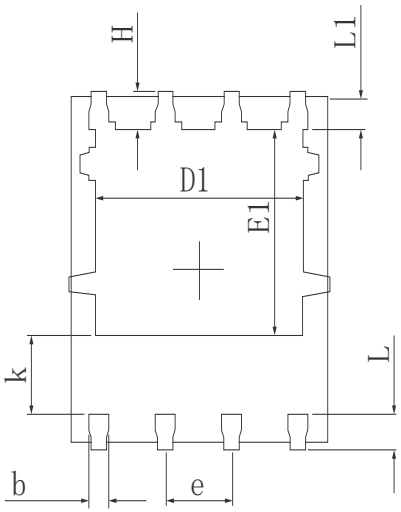
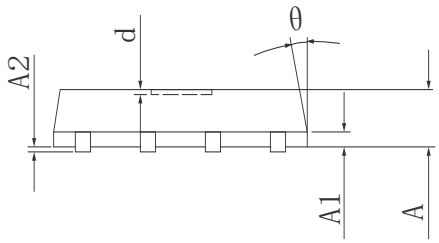


Fig15. Switching Time Test Circuit and waveforms

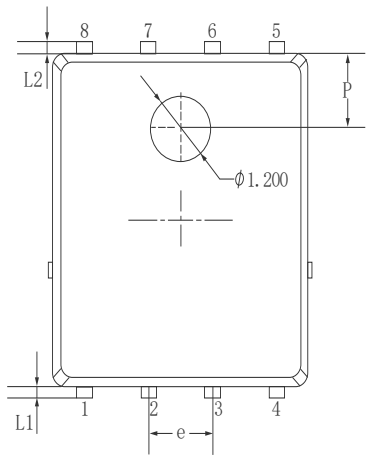
●Dimensions（PDFN5*6）

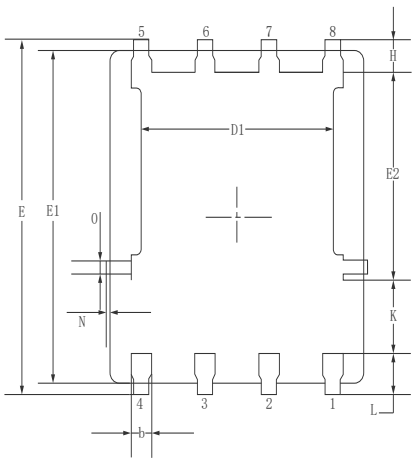


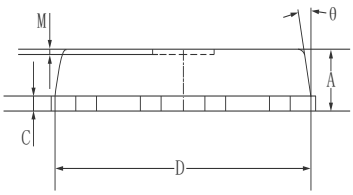




SYMBOL	MILLIMETER		
	MIN	Typ.	MAX
A	0.900	1.000	1.100
A1	0.254 REF.		
A2	0~0.05		
D	4.824	4.900	4.976
D1	3.910	4.010	4.110
D2	4.924	5.000	5.076
E	5.924	6.000	6.076
E1	3.375	3.475	3.575
E2	5.674	5.750	5.826
b	0.350	0.400	0.450
e	1.270 TYP.		
L	0.534	0.610	0.686
L1	0.424	0.500	0.576
L2	1.800 REF.		
k	1.190	1.290	1.390
H	0.549	0.625	0.701
θ	8°	10°	12°
Φ	1.100	1.200	1.300
d			0.100





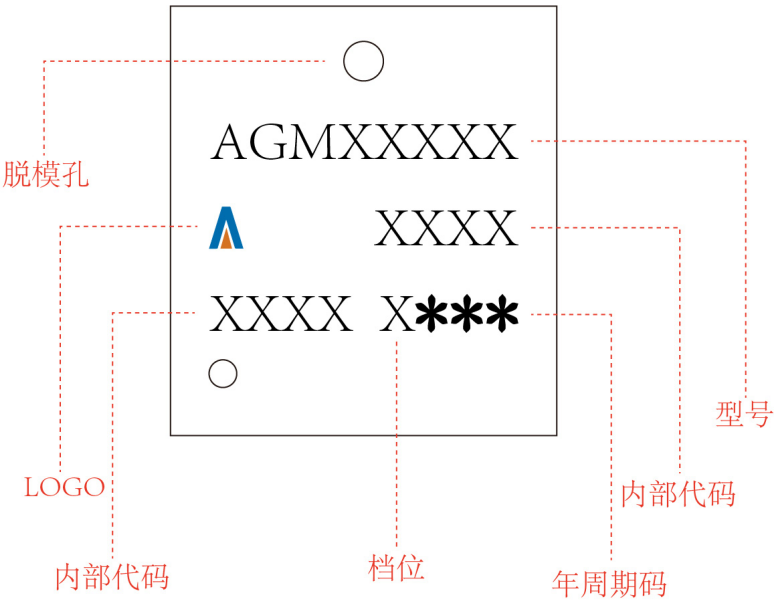


Symbol	Millimeters		
	MIN.	NOM.	MAX.
A	0.90	1.05	1.20
B	0.35	0.40	0.50
C	0.20	0.25	0.35
D	4.90	5.05	5.20
D1	3.72	3.82	3.92
E	6.00	6.15	6.30
E1	5.60	5.75	5.90
E2	3.47	3.57	3.67
e	1.27 BSC.		
H	0.48	0.58	0.68
K	1.17	1.27	1.37
L	0.64	0.74	0.84
L1/L2	0.20 REF.		
θ	8°	10°	12°
M	0.08 REF.		
N	0	-	0.15
O	0.25 REF.		
P	1.28 REF.		

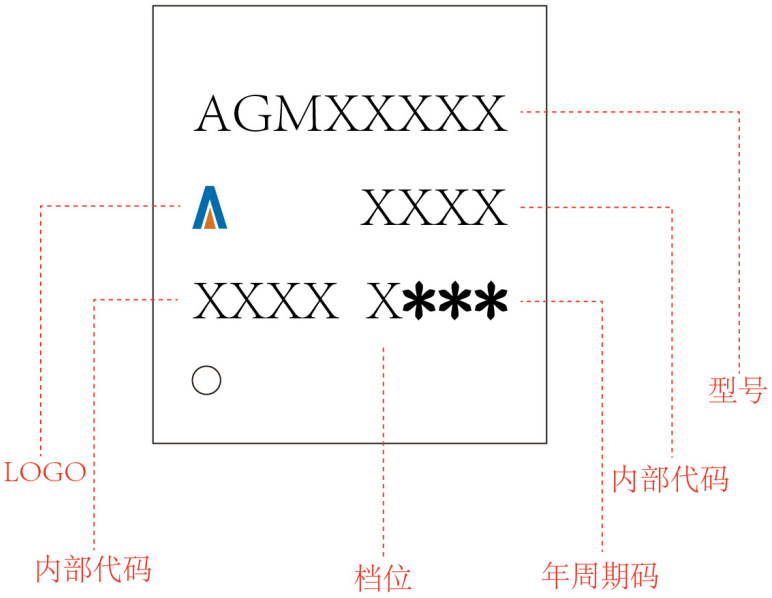
PDFN5*6

Marking Instructions:

Model1:



Model2:



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This document is the fourth version issued on April 10th, 2024. This document replaces all previously provided information.